

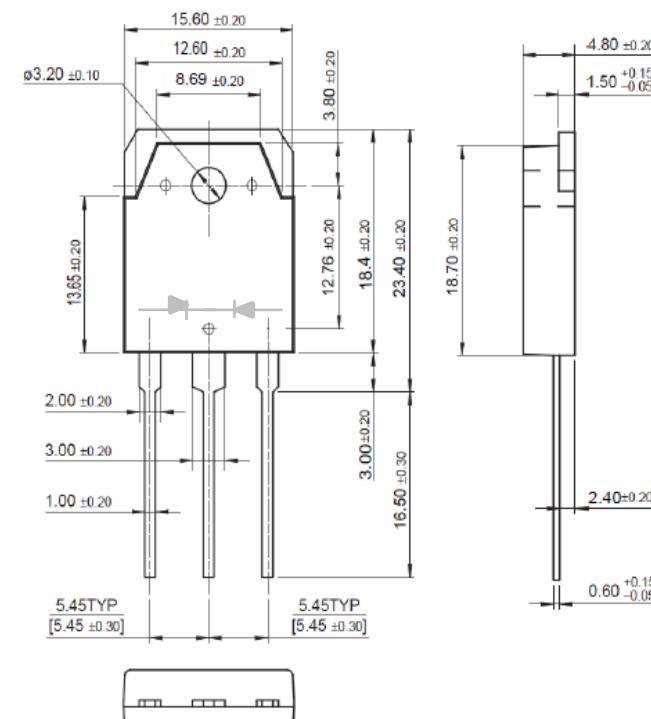
<b>FAST RECOVERY EPITAXIAL DIODE</b>		200V / 20A $V_F=1.1V @ I_F=10A$ , $t_{rr}=34ns$					
<b>PRODUCT FEATURES</b>		<b>TO-3PN</b>					
<ul style="list-style-type: none"> <li>• Ultrafast Recovery Time</li> <li>• Soft Recovery Characteristics</li> <li>• Low Recovery Loss</li> <li>• Low Forward Voltage</li> <li>• High Surge Current Capability</li> <li>• Low Leakage Current</li> </ul>		 <p>Dimensions in millimeter and ( inches )</p>					
<b>APPLICATIONS</b>							
<ul style="list-style-type: none"> <li>• Freewheeling, Snubber, Clamp</li> <li>• Inversion Welder</li> <li>• Plating Power Supply</li> <li>• Ultrasonic Cleaner and Welder</li> </ul>							
<b>MECHANICAL DATA</b>							
<ul style="list-style-type: none"> <li>• Case : TO-3PN Molded Plastic</li> <li>• Epoxy : UL94V-0 rate flame retardant</li> <li>• Polarity : As Marked</li> </ul>							
<b>ABSOLUTE MAXIMUM RATINGS (TC=25°C unless otherwise specified )</b>							
PARAMETER		SYMBOL	VALUES	UNIT			
		Marking	D92-02				
Maximum Repetitive Reverse Voltage		VRM	200	V			
Average Forward Current	T <sub>C</sub> =110°C, Per Diode	I <sub>F(AV)</sub>	10	A			
	T <sub>C</sub> =110°C, Per Package		20				
RMS Forward Current	T <sub>C</sub> =110°C, Per Diode	I <sub>F(RMS)</sub>	14	A			
Non-Repetitive Surge Forward Current	t <sub>p</sub> =10ms, 50Hz, Half Sine Wave	I <sub>FSM</sub>	100	A			
Power Dissipation		P <sub>D</sub>	83	W			
Operating Junction and Storage Temperatures		T <sub>J</sub> , T <sub>STG</sub>	-55 to + 150	°C			
Thermal Resistance	Junction-to-Case	R <sub>θJC</sub>	1.5	°C/W			
Module-to-Sink			1.1	Nt.m			
Weight			5.2	g			
<b>ELECTRICAL AND DYNAMIC RECOVERY CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)</b>							
PARAMETER		TEST CONDITIONS	SYMBOL	Min.	Typ.	Max.	UNIT
Reverse Leakage Current	V <sub>R</sub> =200V		I <sub>RM</sub>	-	-	25	μA
	V <sub>R</sub> =200V, T <sub>J</sub> =125°C			-	-	250	μA
Forward Voltage	I <sub>F</sub> =10A	V <sub>F</sub>	-	0.95	1.1	V	
	I <sub>F</sub> =10A, T <sub>J</sub> =125°C			-	0.95	0.95	V
Reverse Recovery Time	I <sub>F</sub> =1A, V <sub>R</sub> =30V, dI <sub>F</sub> /dt=-200A/μs	trr	-	18	-	ns	
Reverse Recovery Time	V <sub>R</sub> =100V, I <sub>F</sub> =10A dI <sub>F</sub> /dt=-200A/μs, T <sub>J</sub> =25°C	trr	-	34	-	ns	
Max. Reverse Recovery Current			I <sub>RRM</sub>	-	3.2	-	A
Reverse Recovery Time	V <sub>R</sub> =100V, I <sub>F</sub> =10A dI <sub>F</sub> /dt=-200A/μs, T <sub>J</sub> =125°C	trr	-	46	-	ns	
Max. Reverse Recovery Current			I <sub>RRM</sub>	-	4.8	-	A

FIG. 1 - Typical Forward Voltage Drop Characteristics

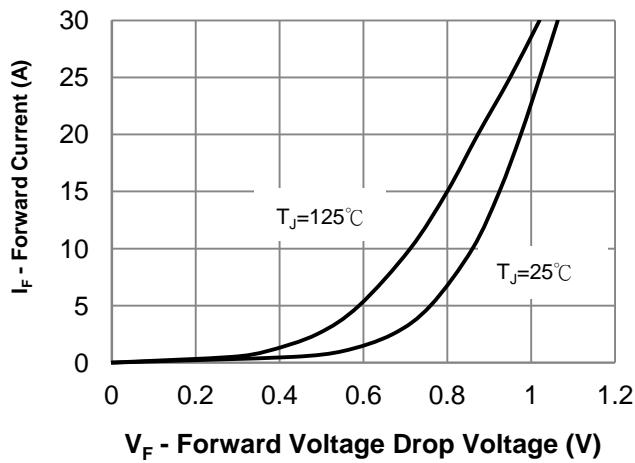


FIG. 2 - Typical Value of Reverse Current vs. Reverse Voltage

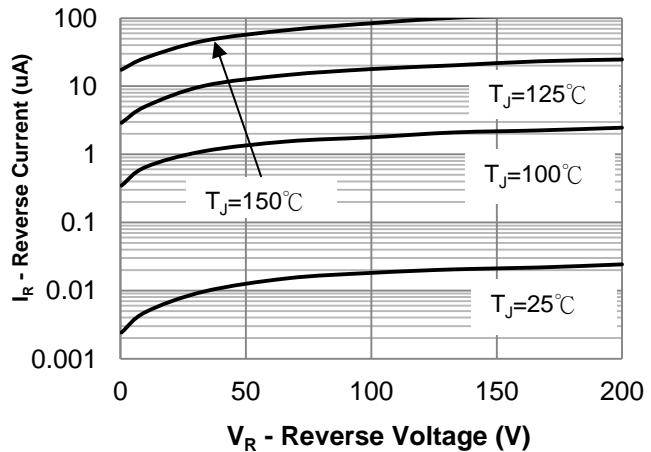


FIG. 3 - Typical Junction Capacitance vs. Reverse Voltage

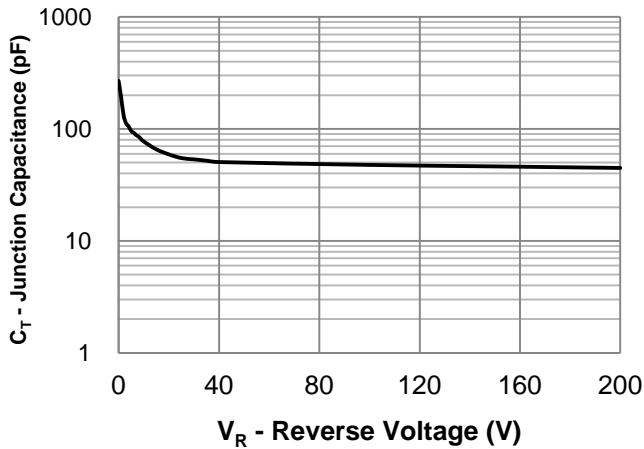


FIG. 4 - Average Forward Current vs. Maximum Allowable Case Temperature

